## Silicon Epitaxial Planar Switching Diode

## Fast Switching Diode



Absolute Maximum Ratings $\left(\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}\right)$

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Peak Reverse Voltage | $\mathrm{V}_{\mathrm{RM}}$ | 100 | V |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 80 | V |
| Average Rectified Forward Current | $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | 150 | mA |
| Forward Continuous Current | $\mathrm{I}_{\mathrm{FM}}$ | 300 | mA |
| Non-Repetitive Peak Forward Surge Current (at $\mathrm{t}=1 \mu \mathrm{~s})$ | $\mathrm{I}_{\mathrm{FSM}}$ | 4 | A |
| Power Dissipation | $\mathrm{P}_{\mathrm{d}}$ | 400 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Forward Voltage } \\ & \text { at } I_{F}=5 \mathrm{~mA} \\ & \text { at } I_{F}=10 \mathrm{~mA} \\ & \text { at } I_{F}=100 \mathrm{~mA} \\ & \text { at } I_{F}=150 \mathrm{~mA} \end{aligned}$ | $V_{F}$ | $\begin{gathered} 0.62 \\ - \\ - \end{gathered}$ | $\begin{gathered} 0.72 \\ 0.855 \\ 1 \\ 1.25 \end{gathered}$ | V |
| Reverse Leakage Current $\begin{aligned} & \text { at } V_{R}=80 \mathrm{~V} \\ & \text { at } V_{R}=20 \mathrm{~V} \\ & \text { at } V_{R}=75 \mathrm{~V}, T_{J}=150^{\circ} \mathrm{C} \\ & \text { at } V_{R}=25 \mathrm{~V}, \mathrm{~T}_{J}=150^{\circ} \mathrm{C} \end{aligned}$ | $I_{\text {R }}$ |  | $\begin{gathered} 100 \\ 25 \\ 50 \\ 30 \end{gathered}$ | nA <br> nA <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ |
| Reverse Breakdown Voltage at $I_{R}=100 \mu \mathrm{~A}$ | $\mathrm{V}_{(\mathrm{BR}) \mathrm{R}}$ | 80 | - | V |
| Total Capacitance at $\mathrm{V}_{\mathrm{R}}=0.5 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {tot }}$ | - | 4 | pF |
| Reverse Recovery Time at $\mathrm{I}_{\mathrm{F}}=\mathrm{I}_{\mathrm{R}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{r}}=0.1 \mathrm{XI}, \mathrm{I}_{\mathrm{L}}=100 \Omega$ | $\mathrm{trr}_{\text {r }}$ | - | 4 | ns |



## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads SOD-123

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Diodes - General Purpose, Power, Switching category:
Click to view products by Hong Kong Chuangji manufacturer:

Other Similar products are found below :
MCL4151-TR3 MMBD3004S-13-F RD0306T-H DSE010-TR-E BAV17-TR BAV19-TR 1N3611 NTE156A NTE574 NTE6244 1SS181-
TP 1SS400CST2RA SDAA13 SHN2D02FUTW1T1G LS4151GS08 FC903-TR-E 1 N4449 1N456A 1N4934-E3/73 1N914B 1N914BTR
1SS226-TP RFUH20TB3S D291S45T BAV300-TR BAW56DWQ-7-F BAW75-TAP MM230L-CAA IDW40E65D1 JAN1N3600
JAN1N4153-1 JAN1N4454-1 JAN1N4454UR-1 LL4151-GS18 053684A SMMSD4148T3G 707803H NSVDAN222T1G CDSZC01100-HF
LL4150-M-08 1 N4454-TR BAV70HDW-7 BAS28-7 JANTX1N6640 BAW56HDW-13 BAS28 TR VS-HFA04SD60STR-M3 NSVM1MA152WKT1G 1SS388-TP RGP30D-E3/73

